

General Description

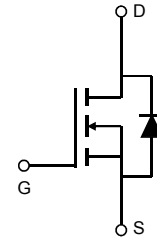
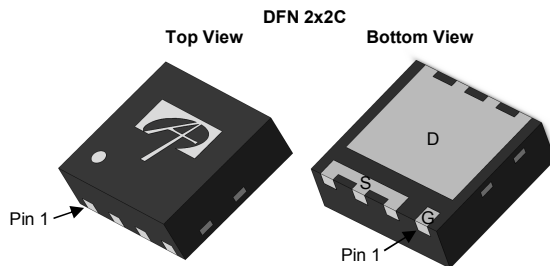
- Trench Power AlphaSGT™ technology
- Low $R_{DS(ON)}$
- Logic driven
- RoHS and Halogen-Free Compliant

Applications

- Home Automation and IoT
- VOIP applications

Product Summary

V_{DS}	100V
I_D (at $V_{GS}=10V$)	8A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 32m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 39m Ω



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AON2392	DFN2x2C	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	8
		$T_A=70^\circ\text{C}$	6
Pulsed Drain Current ^C	I_{DM}	32	A
Power Dissipation ^B	P_D	$T_A=25^\circ\text{C}$	4.1
		$T_A=70^\circ\text{C}$	2.6
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	25	30	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}		45	55	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.4	1.85	2.4	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =8A		26	32	mΩ
		T _J =125°C		46	57	
		V _{GS} =4.5V, I _D =6A		31	39	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =8A		25		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.74	1	V
I _S	Maximum Body-Diode Continuous Current				5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V, f=1MHz		840		pF
C _{oss}	Output Capacitance			64		pF
C _{rss}	Reverse Transfer Capacitance			4		pF
R _g	Gate resistance	f=1MHz		1.4		Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =50V, I _D =8A		12.8	25	nC
Q _{g(4.5V)}	Total Gate Charge			6.1	12	nC
Q _{gs}	Gate Source Charge			2.1		nC
Q _{gd}	Gate Drain Charge			1.8		nC
Q _{oss}	Output Charge	V _{GS} =0V, V _{DS} =50V		11		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =50V, R _L =5.85Ω, R _{GEN} =3Ω		7		ns
t _r	Turn-On Rise Time			8		ns
t _{D(off)}	Turn-Off DelayTime			24		ns
t _f	Turn-Off Fall Time			3		ns
t _{rr}	Body Diode Reverse Recovery Time		I _F =8A, di/dt=500A/μs		20	
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =8A, di/dt=500A/μs		70		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

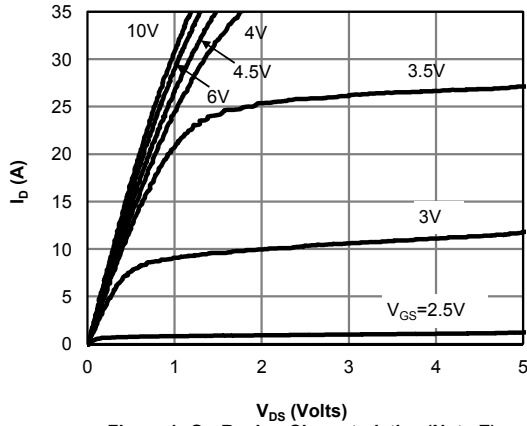


Figure 1: On-Region Characteristics (Note E)

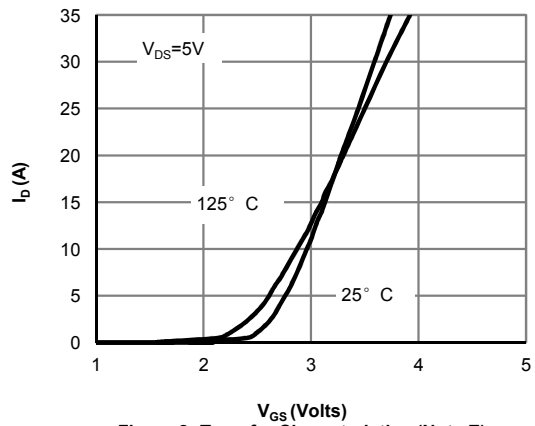


Figure 2: Transfer Characteristics (Note E)

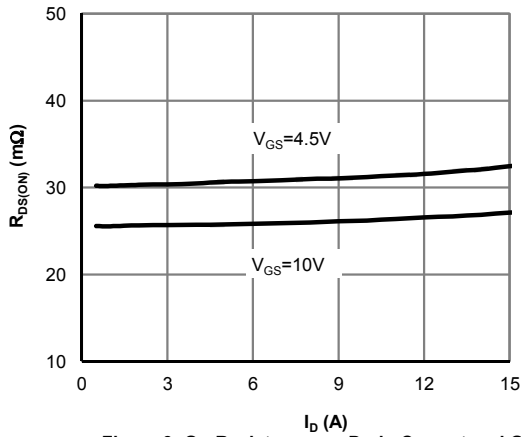


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

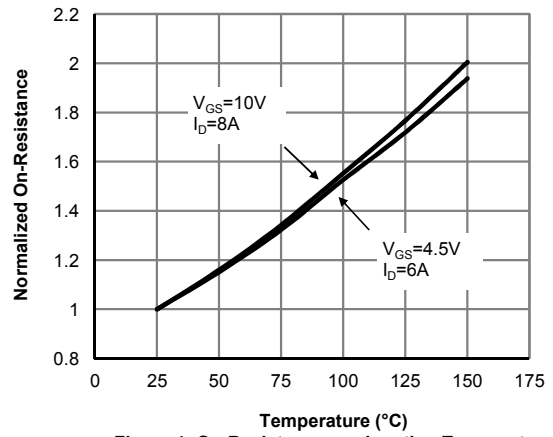


Figure 4: On-Resistance vs. Junction Temperature (Note E)

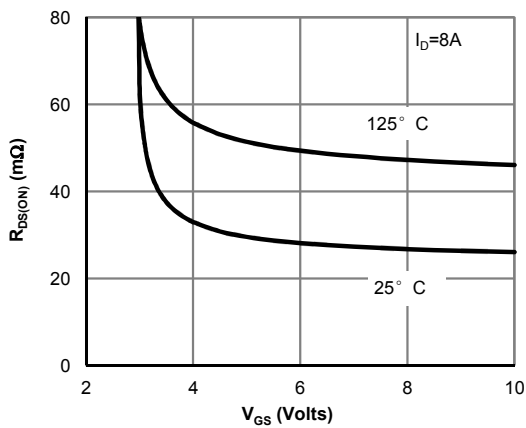


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

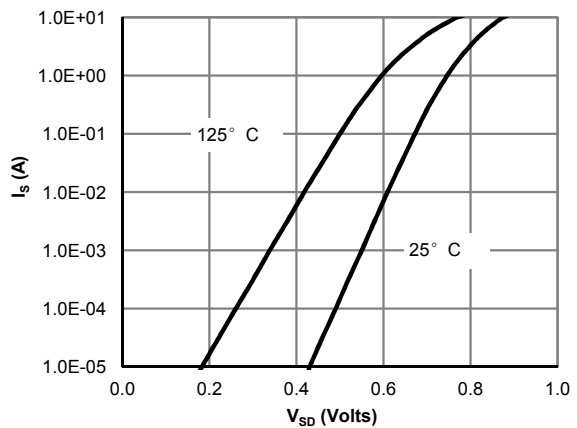


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

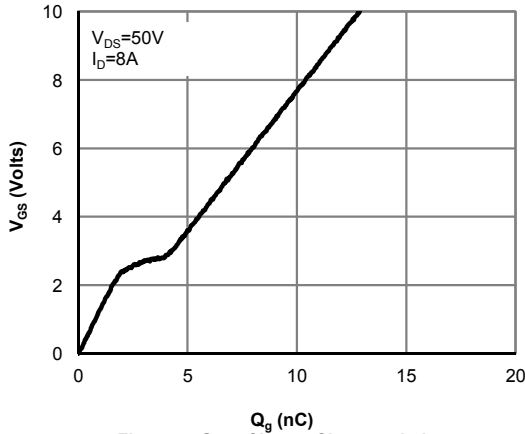


Figure 7: Gate-Charge Characteristics

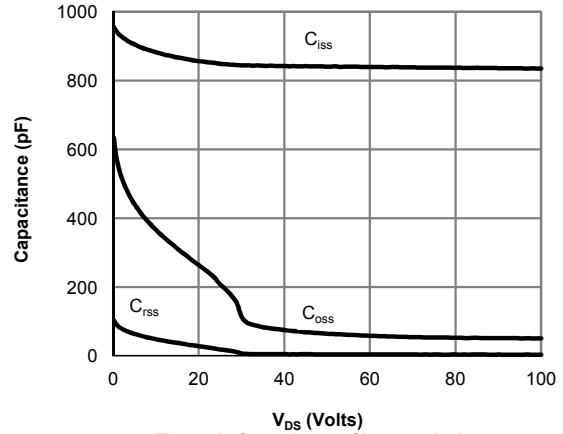


Figure 8: Capacitance Characteristics

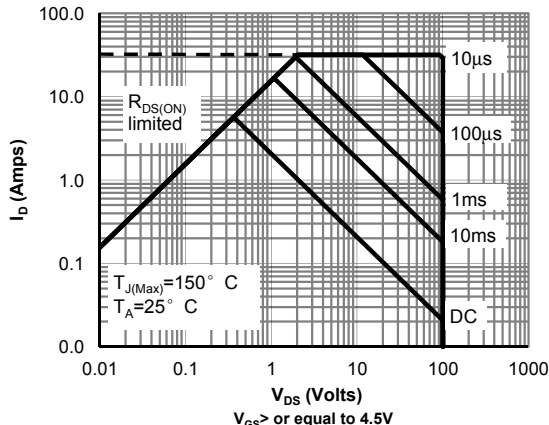


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

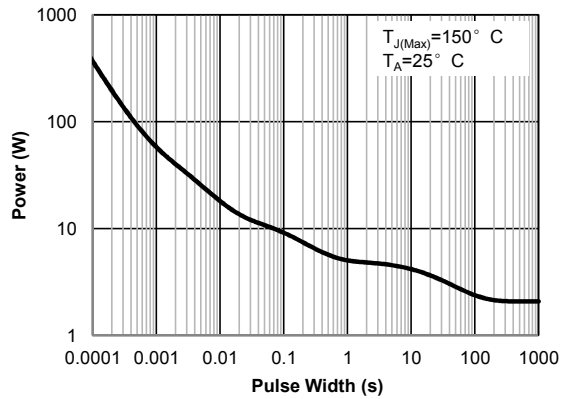


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

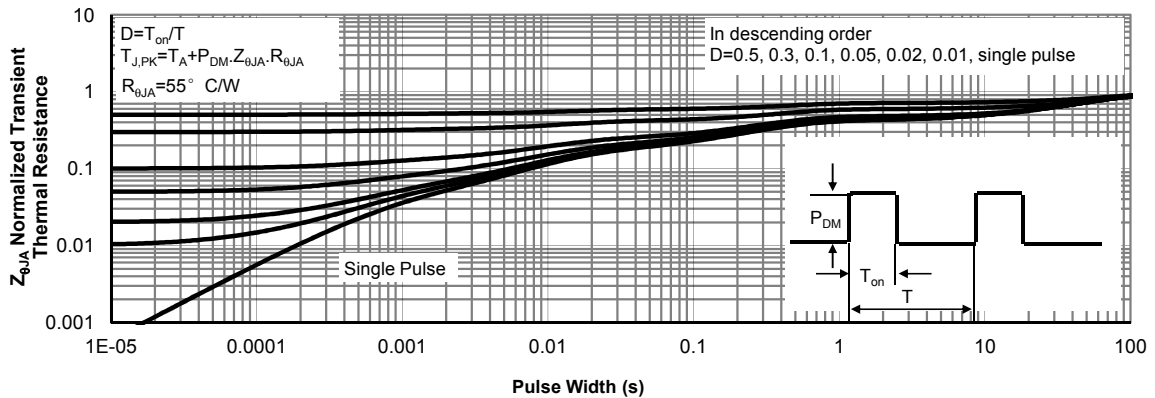


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Figure A: Gate Charge Test Circuit & Waveforms

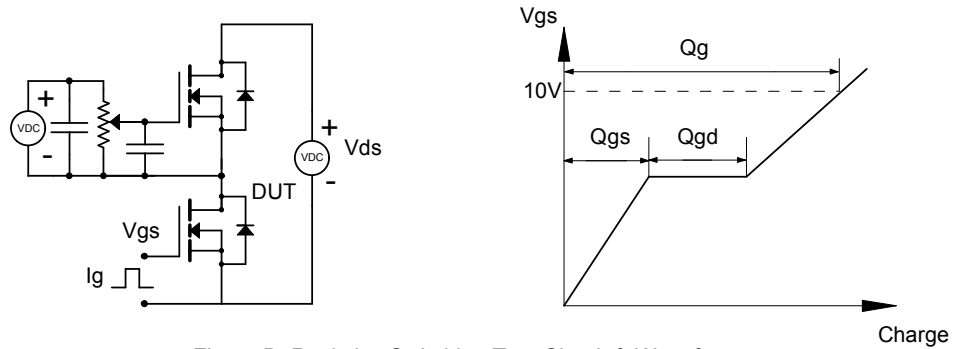


Figure B: Resistive Switching Test Circuit & Waveforms

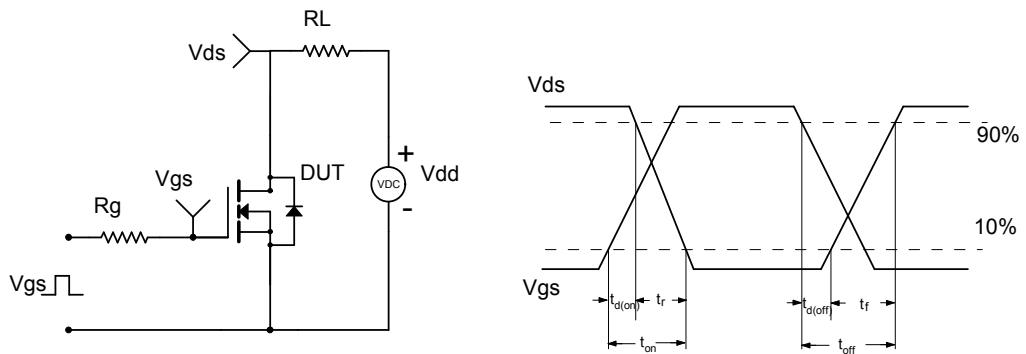


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

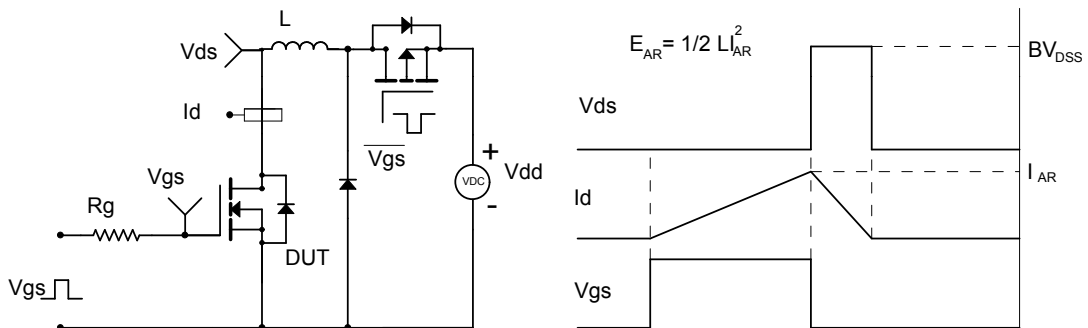
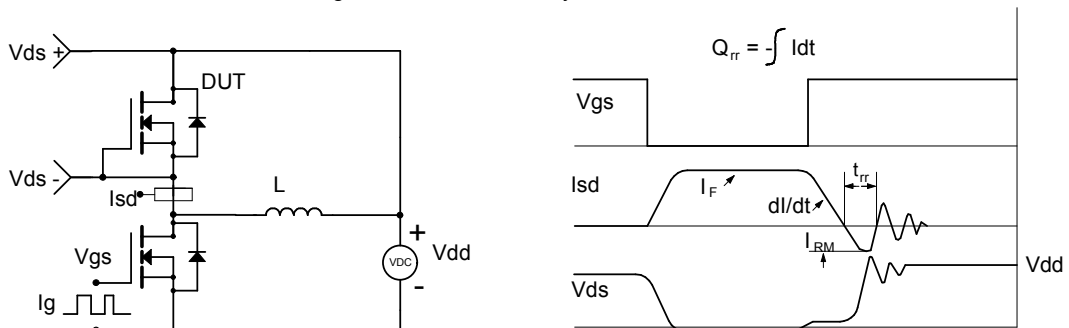


Figure D: Diode Recovery Test Circuit & Waveforms



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